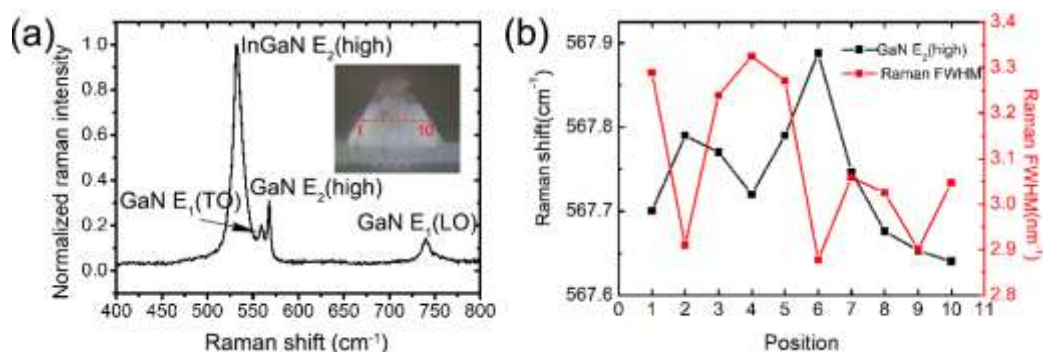


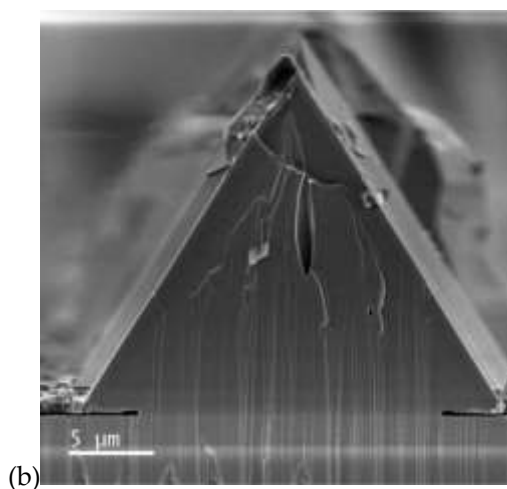
Supporting information for

Efficient carrier recombination in InGaN pyramidal μ -LED obtained by selective area growth

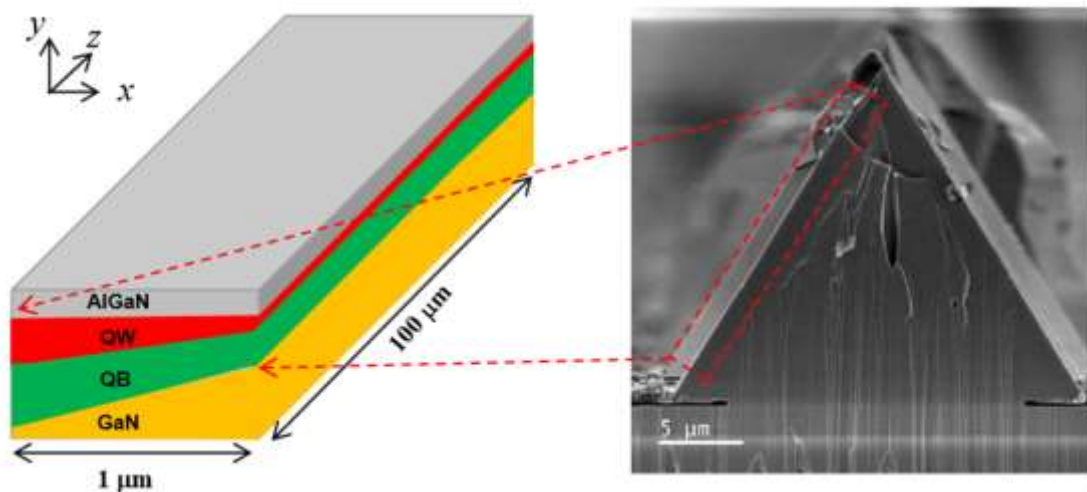
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Supplementary Figure S1. Raman spectrum taken from the cross-sectional GaN pyramid (a), the inserted image shows the optical image of the GaN pyramid and positions where Raman spectroscopy was taken; The Raman shift and corresponding FWHM values of the GaN E₂ (high) peak from above 10 positions on the pyramid



Supplementary Figure S2. Cross-sectional SEM image of the pyramidal GaN overgrowing on SiO₂ mask (chemically etched away)



Supplementary Figure S3. The correlation between the simulation structure and the SEM cross-sectional image of the pyramid